Silicon N Channel MOS FET High Speed Power Switching

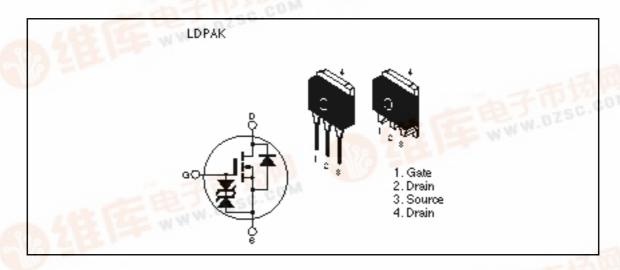
# HITACHI

ADE-208-567 Target specification 1st. Edition

#### **Features**

- Low on-resistance  $R_{DS(on)} = 7m$  typ.
- 4V gate drive devices.
- · High speed switching

#### **Outline**





#### **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	50	A
Drain peak current	I <sub>D(pulse)</sub> *1	200	A
Body to drain diode reverse drain current	I <sub>DR</sub>	50	A
Channel dissipation	Pch*2	75	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10µs, duty cycle 1 %

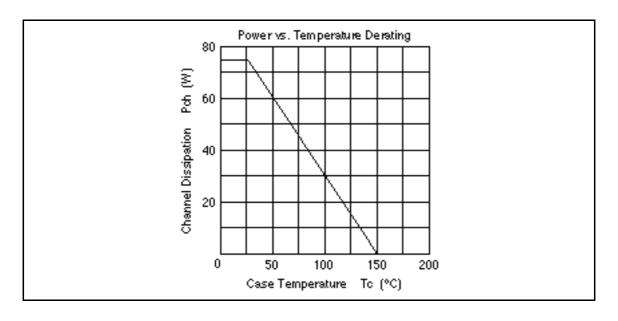
2. Value at Tc = 25°C

#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \mu A, V_{DS} = 0$
Zero gate voltege drain current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{\text{DS}} = 30 \text{ V}, V_{\text{GS}} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_D = 1 \text{mA}, V_{DS} = 10 \text{V}$
Static drain to source on state	R <sub>DS(on)</sub>	_	7.0	10	m	$I_D = 25A, V_{GS} = 10V^{*1}$
resistance	R <sub>DS(on)</sub>	_	12	18	m	$I_D = 25A, V_{GS} = 4V^{*1}$
Forward transfer admittance	y <sub>fs</sub>	25	45	_	S	$I_D = 25A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	_	2000	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	1500	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	350	_	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	_	20	_	ns	$V_{GS} = 10V, I_{D} = 25A$
Rise time	t <sub>r</sub>	_	330	_	ns	$R_{L} = 0.4$
Turn-off delay time	$t_{d(off)}$	_	190	_	ns	_
Fall time	t <sub>f</sub>	_	190	_	ns	_
Body to drain diode forward voltage	$V_{DF}$		0.95	_	V	$I_{D} = 50A, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	_	140	_	ns	$I_F = 50A, V_{GS} = 0$ diF/ dt = 50A/µs

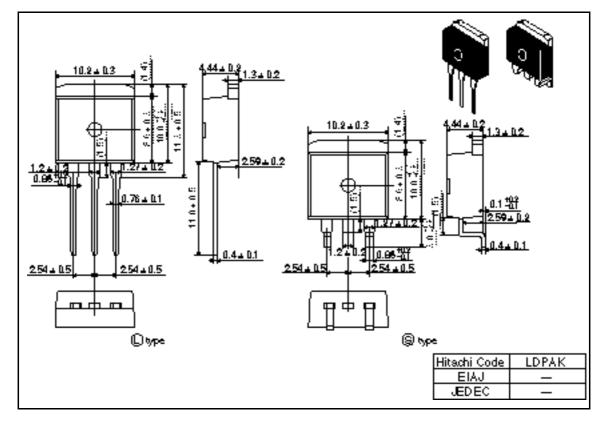
Note: 1. Pulse test

### **Main Characteristics**



### **Package Dimensions**

Unit: mm



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